

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
an insulating film, a capacitor formed on the
insulating film and comprising a bottom electrode,
5 a top electrode, and a dielectric film between the top
electrode and the bottom electrode, a plug passing
through the insulating film and connected to the bottom
electrode, and an oxygen barrier film covering the
capacitor and the insulating film, and having lower
10 oxygen permeability than the insulating film.